



January 1999 Revised August 2001

# 74LVT16245 • 74LVTH16245 Low Voltage 16-Bit Transceiver with 3-STATE Outputs

#### **General Description**

The LVT16245 and LVTH16245 contain sixteen non-inverting bidirectional buffers with 3-STATE outputs and is intended for bus oriented applications. The device is byte controlled. Each byte has separate control inputs which can be shorted together for full 16-bit operation. The T/R inputs determine the direction of data flow through the device. The  $\overline{OE}$  inputs disable both the A and B ports by placing them in a high impedance state.

The LVTH16245 data inputs include bushold, eliminating the need for external pull-up resistors to hold unused inputs.

These non-inverting transceivers are designed for low-voltage (3.3V) V<sub>CC</sub> applications, but with the capability to provide a TTL interface to a 5V environment. The LVT16245 and LVTH16245 are fabricated with an advanced BicMOS technology to achieve high speed operation similar to 5V ABT while maintaining low power dissipation.

#### **Features**

- Input and output interface capability to systems at 5V V<sub>CC</sub>
- Bushold data inputs eliminate the need for external pull-up resistors to hold unused inputs (74LVTH16245), also available without bushold feature (74LVT16245).
- Live insertion/extraction permitted
- Power Up/Down high impedance provides glitch-free bus loading

4LVT16245 • 74LVTH16245 Low Voltage 16-Bit Transceiver with 3-STATE Outputs

- Outputs source/sink –32 mA/+64 mA
- Functionally compatible with the 74 series 16245
- Latch-up performance exceeds 500 mA
- ESD performance: Human-body model >2000V Machine model >200V
- Charged-device >1000V

A12 A13 A14 A15

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T/R

 Also packaged in plastic Fine-Pitch Ball Grid Array (FBGA) (Preliminary)

## **Ordering Code:**

Order Number Package Number		Package Description			
74LVT16245GX (Note 1)	BGA54A (Preliminary)	54-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide [Tape and Reel]			
74LVT16245MEA (Note 2)	MS48A	48-Lead Small Shrink Outline Package (SSOP), JEDEC MO-118, 0.300" Wide			
74LVT16245MTD (Note 2)	MTD48	48-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 6.1mm Wide			
74LVTH16245GX (Note 1)	BGA54A (Preliminary)	54-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide [Tape and Reel]			
74LVTH16245MEA (Note 2)	MS48A	48-Lead Small Shrink Outline Package (SSOP), JEDEC MO-118, 0.300" Wide			
74LVTH16245MTD (Note 2)	MTD48	48-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 6.1mm Wide			

B<sub>3</sub> B<sub>4</sub> B<sub>5</sub> B<sub>6</sub> B<sub>7</sub> B<sub>8</sub> B<sub>9</sub> B<sub>10</sub> B<sub>11</sub> B<sub>12</sub> B<sub>13</sub> B<sub>14</sub>

Note 1: BGA package available in Tape and Reel only.

Note 2: Devices also available in Tape and Reel. Specify by appending suffix letter "X" to the ordering code.

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#### Logic Symbol



-O DE

Connection D	liagrams	
Pin Assignm	ent for SSOP	and TSSOP
T/R,		8 - 0E1
в <sub>о</sub> —	2 4	7 – A <sub>0</sub>
в, —	3 4	6 — A <sub>1</sub>
GND —	4 4	
в <sub>2</sub> —	5 4	2
в <sub>3</sub> —	6 4	0
V <sub>cc</sub> —	7 4 8 4	00
в <sub>4</sub> — в <sub>5</sub> —	o 4 9 4	
	10 3	5
в <sub>6</sub> —		8 — A <sub>6</sub>
в <sub>7</sub> —	12 3	
в <sub>а</sub> —	13 3	6 — A <sub>8</sub>
в <sub>9</sub> —	14 3	5 — Ag
GND —	15 3	4 — GND
B <sub>10</sub> —	16 3	3 — A <sub>10</sub>
B <sub>11</sub> —	17 3	
v <sub>cc</sub> —	18 3	00
B <sub>12</sub> —		0 — A <sub>12</sub>
B <sub>1 3</sub> — GND —		9 — A <sub>13</sub> 8 — GND
B <sub>14</sub> —	22 2	
B <sub>15</sub> —	23 2	
T/R <sub>2</sub>	24 2	
Pin As	signment for I	 FBGA
	12345	6
	00000	
8		
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0 0		ŏ
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т	00000	Ó
ר	00000	0
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## **Pin Descriptions**

Pin Names	Description
<del>OE</del> n	Output Enable Input (Active LOW)
T/R <sub>n</sub>	Transmit/Receive Input
A <sub>0</sub> -A <sub>15</sub> B <sub>0</sub> -B <sub>15</sub>	Side A Inputs/3-STATE Outputs
B <sub>0</sub> -B <sub>15</sub>	Side B Inputs/3-STATE Outputs
NC	No Connect

## **FBGA Pin Assignments**

	1	2	3	4	5	6
Α	B <sub>0</sub>	NC	T/R <sub>1</sub>	OE <sub>1</sub>	NC	A <sub>0</sub>
В	B <sub>2</sub>	B <sub>1</sub>	NC	NC	A <sub>1</sub>	A <sub>2</sub>
С	B <sub>4</sub>	B <sub>3</sub>	V <sub>CC</sub>	V <sub>CC</sub>	A <sub>3</sub>	A <sub>4</sub>
D	B <sub>6</sub>	B <sub>5</sub>	GND	GND	A <sub>5</sub>	A <sub>6</sub>
Е	B <sub>8</sub>	B <sub>7</sub>	GND	GND	A <sub>7</sub>	A <sub>8</sub>
F	B <sub>10</sub>	B <sub>9</sub>	GND	GND	A <sub>9</sub>	A <sub>10</sub>
G	B <sub>12</sub>	B <sub>11</sub>	V <sub>CC</sub>	V <sub>CC</sub>	A <sub>11</sub>	A <sub>12</sub>
Н	B <sub>14</sub>	B <sub>13</sub>	NC	NC	A <sub>13</sub>	A <sub>14</sub>
J	B <sub>15</sub>	NC	$T/\overline{R}_2$	OE <sub>2</sub>	NC	A <sub>15</sub>

## **Truth Tables**

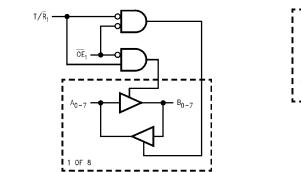
Inp	outs	Outputs		
OE <sub>1</sub>	T/R <sub>1</sub>	Outputs		
L	L	Bus B <sub>0</sub> –B <sub>7</sub> Data to Bus A <sub>0</sub> –A <sub>7</sub>		
L	Н	Bus $A_0 - A_7$ Data to Bus $B_0 - B_7$		
н	Х	HIGH–Z State on A <sub>0</sub> –A <sub>7</sub> ,B <sub>0</sub> –B <sub>7</sub>		
Inp	outs	<b>0</b> / . / .		
	outs T/R <sub>2</sub>	Outputs		
<u> </u>		Outputs Bus B <sub>8</sub> –B <sub>15</sub> Data to Bus A <sub>8</sub> –A <sub>15</sub>		
<u> </u>				

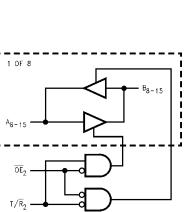
H = HIGH Voltage Level L = LOW Voltage Level X = Immaterial Z = High Impedance

## **Functional Description**

The LVT16245 and LVTH16245 contain sixteen non-inverting bidirectional buffers with 3-STATE outputs. The device is byte controlled with each byte functioning identically, but independent of the other. The control pins can be shorted together to obtain full 16-bit operation.

#### **Logic Diagrams**





Note: Please note that these diagrams are provided only for the understanding of logic operations and should not be used to estimate propagation delays.

## Absolute Maximum Ratings(Note 3)

Symbol	Parameter	Value	Conditions	Units
V <sub>CC</sub>	Supply Voltage	-0.5 to +4.6		V
VI	DC Input Voltage	-0.5 to +7.0		V
Vo	Output Voltage	-0.5 to +7.0	Output in 3-STATE	V
		-0.5 to +7.0 Output in HIGH or LOW S	Output in HIGH or LOW State (Note 4)	v
ік	DC Input Diode Current	-50	V <sub>I</sub> < GND	mA
l <sub>ок</sub>	DC Output Diode Current	-50	V <sub>O</sub> < GND	mA
0	DC Output Current	64	Output at HIGH State, V <sub>O</sub> > V <sub>CC</sub>	
		128	Output at LOW State, V <sub>O</sub> > V <sub>CC</sub>	mA
I <sub>CC</sub>	DC Supply Current per Supply Pin	±64		mA
GND	DC Ground Current per Ground Pin	±128		mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150		°C

## **Recommended Operating Conditions**

Symbol	Parameter	Min	Max	Units
/ <sub>cc</sub>	Supply Voltage	2.7	3.6	V
/ <sub>I</sub>	Input Voltage	0	5.5	V
НС	HIGH-Level Output Current		-32	mA
OL	LOW-Level Output Current		64	mA
A	Free-Air Operating Temperature	-40	+85	°C
Δt/ΔV	Input Edge Rate, V <sub>IN</sub> = 0.8V–2.0V, V <sub>CC</sub> = 3.0V	0	10	ns/V

Note 3: Absolute Maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum rated conditions is not implied.

Note 4:  $\mathrm{I}_{\mathrm{O}}$  Absolute Maximum Ratings must be observed.

### **DC Electrical Characteristics**

Symbol	Paramete		V <sub>CC</sub>	T <sub>A</sub> = -40°C	C to +85°C	Units	Conditions
Symbol	Paramete	Г	(V)	Min	Мах	Units	Conditions
V <sub>IK</sub>	Input Clamp Diode Voltage		2.7		-1.2	V	I <sub>I</sub> = -18 mA
VIH	Input HIGH Voltage		2.7-3.6	2.0		V	$V_0 \le 0.1V$ or
VIL	Input LOW Voltage		2.7-3.6		0.8	V	$V_O \ge V_{CC} - 0.1V$
V <sub>ОН</sub>	Output HIGH Voltage		2.7–3.6	V <sub>CC</sub> - 0.2			I <sub>OH</sub> = -100 μA
			2.7	2.4		V	I <sub>OH</sub> = -8 mA
			3.0	2.0			I <sub>OH</sub> = -32 mA
V <sub>OL</sub>	Output LOW Voltage		2.7		0.2		I <sub>OL</sub> = 100 μA
			2.7		0.5		I <sub>OL</sub> = 24 mA
			3.0		0.4	V	I <sub>OL</sub> = 16 mA
			3.0		0.5	Ï	I <sub>OL</sub> = 32 mA
			3.0		0.55		I <sub>OL</sub> = 64 mA
I <sub>I(HOLD)</sub>	Bushold Input Minimum Drive		3.0	75		μA	$V_{I} = 0.8V$
(Note 5)			0.0	-75		μΛ	$V_{l} = 2.0V$
I <sub>I(OD)</sub>	Bushold Input Over-Drive		3.0	500		μA	(Note 6)
(Note 5)	Current to Change State		5.0	-500			(Note 7)
I <sub>I</sub>	Input Current		3.6		10		$V_{I} = 5.5V$
		Control Pins	3.6		±1	μA	$V_I = 0V \text{ or } V_{CC}$
		Data Pins	3.6		-5	μΛ	$V_I = 0V$
		Data Tina	311113 0.0		1		$V_I = V_{CC}$
I <sub>OFF</sub>	Power Off Leakage Current		0		±100	μΑ	$0V \le V_I \text{ or } V_O \le 5.5V$
I <sub>PU/PD</sub>	Power Up/Down 3-STATE		0-1.5		±100	μA	V <sub>O</sub> = 0.5V to 3.0V
	Output Current		0-1.5		±100	μΛ	$V_I = GND \text{ or } V_{CC}$
I <sub>OZL</sub>	3-STATE Output Leakage Co	urrent	3.6		-5	μΑ	V <sub>O</sub> = 0.5V
I <sub>OZL</sub> (Note 5)	3-STATE Output Leakage Cu	urrent	3.6		-5	μA	$V_0 = 0.0V$

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## DC Electrical Characteristics (Continued)

Symbol	Parameter	V <sub>CC</sub>	$T_A = -40^{\circ}C$ to $+85^{\circ}C$		Units	Conditions
Symbol	Faranieter	(V)	Min	Max	Units	Conditions
I <sub>OZH</sub>	3-STATE Output Leakage Current	3.6		5	μA	V <sub>O</sub> = 3.0V
I <sub>OZH</sub> (Note 5)	3-STATE Output Leakage Current	3.6		5	μΑ	V <sub>O</sub> = 3.6V
I <sub>OZH</sub> +	3-STATE Output Leakage Current	3.6		10	μA	$V_{CC} < V_O \le 5.5V$
I <sub>CCH</sub>	Power Supply Current	3.6		0.19	mA	Outputs HIGH
I <sub>CCL</sub>	Power Supply Current	3.6		5.0	mA	Outputs LOW
I <sub>CCZ</sub>	Power Supply Current	3.6		0.19	mA	Outputs Disabled
I <sub>CCZ</sub> +	Power Supply Current	3.6		0.19	mA	$V_{CC} \le V_O \le 5.5V$ , Outputs Disabled
∆I <sub>CC</sub> (Note 8)	Increase in Power Supply Current	3.6		0.2	mA	One Input at $V_{CC} - 0.6V$ Other Inputs at $V_{CC}$ or GND

Note 5: Applies to bushold versions only (74LVTH16245).

Note 6: An external driver must source at least the specified current to switch from LOW-to-HIGH.

Note 7: An external driver must sink at least the specified current to switch from HIGH-to-LOW. Note 8: This is the increase in supply current for each input that is at the specified voltage level rather than  $V_{CC}$  or GND.

## Dynamic Switching Characteristics (Note 9)

Symbol	Parameter	v <sub>cc</sub>	T <sub>A</sub> = 25°C		Units	Conditions	
Symbol	Faranieter	(V)	Min	Тур	Max	Units	$\textbf{C}_{\textbf{L}}=\textbf{50}~\textbf{pF},~\textbf{R}_{\textbf{L}}=\textbf{500}\Omega$
V <sub>OLP</sub>	Quiet Output Maximum Dynamic $V_{OL}$	3.3		0.8		V	(Note 10)
V <sub>OLV</sub>	Quiet Output Minimum Dynamic $V_{OL}$	3.3		-0.8		V	(Note 10)

Note 9: Characterized in SSOP package. Guaranteed parameter, but not tested.

Note 10: Max number of outputs defined as (n). n-1 data inputs are driven 0V to 3V. Output under test held LOW.

## **AC Electrical Characteristics**

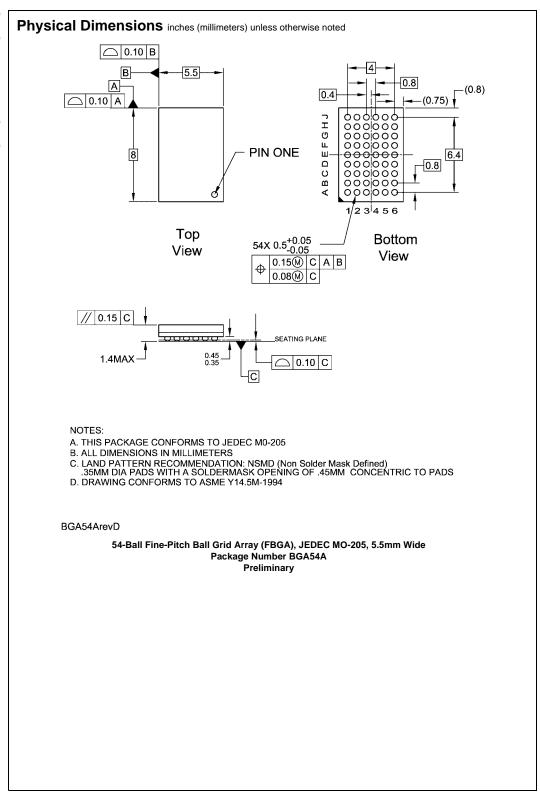
Symbol	Parameter	V <sub>CC</sub> = 3.	3V ± 0.3V	R <sub>L</sub> = 500Ω	= 2.7V	Units
		Min	Max	Min	Max	
t <sub>PLH</sub>	Propagation Delay Data to Output	1.5	3.5	1.5	3.9	
t <sub>PHL</sub>		1.3	3.5	1.3	3.9	ns
t <sub>PZH</sub>	Output Enable Time	1.5	4.5	1.5	5.3	ns
t <sub>PZL</sub>		1.6	5.3	1.6	6.9	115
t <sub>PHZ</sub>	Output Disable Time	2.3	5.4	2.3	6.1	ns
t <sub>PLZ</sub>		2.2	5.1	2.2	5.4	115
t <sub>OSHL</sub>	Output to Output Skew		1.0		1.0	ns
t <sub>OSLH</sub>	(Note 11)		1.0		1.0	115

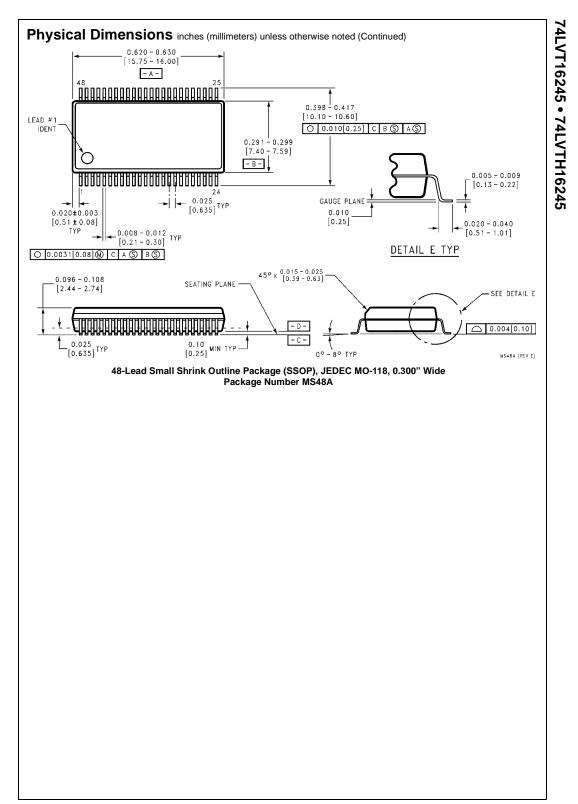
Note 11: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t<sub>OSHL</sub>) or LOW-to-HIGH (t<sub>OSLH</sub>). Parameter guaranteed by design.

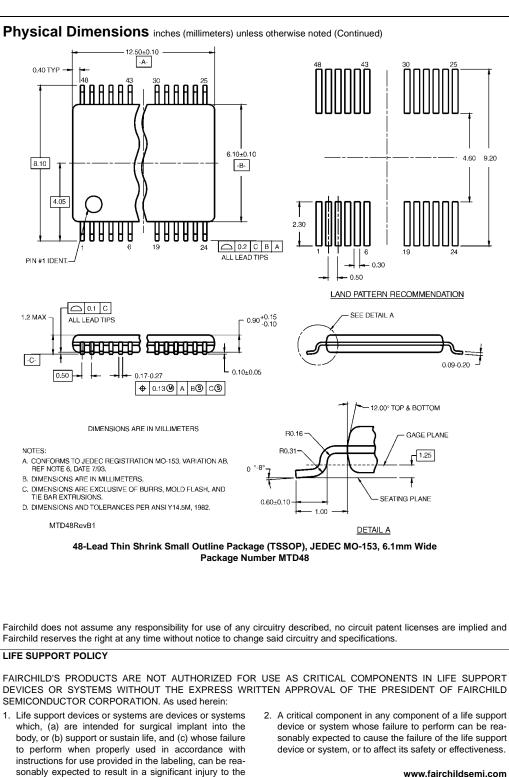
#### Capacitance (Note 12)

Symbol	Parameter	Conditions	Typical	Units
C <sub>IN</sub>	Input Capacitance	$V_{CC} = 0V, V_I = 0V \text{ or } V_{CC}$	4	pF
C <sub>I/O</sub>	Input/Output Capacitance	$V_{CC} = 3.0V, V_O = 0V \text{ or } V_{CC}$	8	pF

Note 12: Capacitance is measured at frequency f = 1 MHz, per MIL-STD-883, Method 3012







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